Abstracts

A Q-Band Monolithic Three-Stage Amplifier

J. Yonaki, M. Aust, K. Nakano, G. Dow, L.C.T Liu, E. Hsieh, R. Dia and H.C. Yen. "A Q-Band Monolithic Three-Stage Amplifier." 1988 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 88.1 (1988 [MCS]): 91-94.

A Q-band High Electron Mobility Transistor (HEMT) amplifier has been designed and fabricated. This three stage circuit utilizes 0.2 x 60 micron HEMT devices. The amplifier has a measured gain of over 10 dB from 42 to 47.5 GHz and a peak gain of 16 dB at 44.5 GHz. This result represents the state-of-the-art monolithic HEMT amplifier performance.

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